

Ainorkhilah Mahmood

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/844204/publications.pdf>

Version: 2024-02-01

18
papers

31
citations

2682572

2
h-index

2272923

4
g-index

18
all docs

18
docs citations

18
times ranked

26
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of Porosity on the Characteristics of GaN Grown on Sapphire. , 2011, , .		5
2	Applications of the image processing method on the structure measurements in porous GaN. Journal of Experimental Nanoscience, 2014, 9, 87-95.	2.4	5
3	The effect of etching duration on structural properties of porous Si fabricated by a new two-steps alternating current photo-assisted electrochemical etching (ACPEC) technique for MSM photodetector. , 2017, , .		5
4	Quantum Confinement of Integrated Pulse Electrochemical Etching of Porous Silicon for Metal Semiconductor Metal Photodetector. Materials Science Forum, 0, 846, 245-255.	0.3	3
5	Structural and Optical Studies of Undoped Porous GaN Prepared by Pt-Assisted Electroless Etching. Materials Science Forum, 2016, 846, 358-365.	0.3	2
6	Study of low dimensional SiGe island on Si for potential visible Metal-Semiconductor-Metal photodetector. EPJ Web of Conferences, 2017, 162, 01062.	0.3	2
7	Crystal orientation dependence of alternating current photo-assisted (ACPEC) porous silicon for potential optoelectronic application. Microelectronics International, 2019, 37, 46-53.	0.6	2
8	Influence of different etching methods on the structural properties of porous silicon. Microelectronics International, 2022, 39, 101-109.	0.6	2
9	Photoluminescence, raman and X-ray diffraction studies of porous GaN grown on sapphire. , 2011, , .		1
10	Applications of image processing (IP) method on the structure measurements in porous GaN. , 2012, , .		1
11	Investigation on the Effect of Crystal Orientation Dependence of Pulse Porous Silicon for White Light Emission. Key Engineering Materials, 0, 701, 164-176.	0.4	1
12	Enhancing Performance of Porous Si-Doped GaN Based MSM Photodetector Using 50 Hz ACPEC. Journal of Physics: Conference Series, 2020, 1535, 012006.	0.4	1
13	Morphological, Structural and Optical Characteristics of Porous GaN Fabricated by UV-Assisted Electrochemical Etching. Solid State Phenomena, 2020, 301, 3-11.	0.3	1
14	Effect of porosity on the characteristics of GaN grown on sapphire. , 2010, , .		0
15	Visible Luminescence of Nanoporous Silicon Using Alternating Current Photo-Assisted Electrochemical Etching for Potential MSM Photodetector. Materials Science Forum, 0, 846, 274-282.	0.3	0
16	Structural Characterization on Different Type of Silicon Wafer on The Formation of Porous Silicon Structure. Journal of Physics: Conference Series, 2020, 1535, 012033.	0.4	0
17	Porosification Analysis on the Effect of Resistivity Dependence on N-Type Pulsed Porous Silicon. Solid State Phenomena, 0, 301, 12-17.	0.3	0
18	The Role of Alternating Current on Photo-Assisted Electrochemical Porosification of GaN. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 287-290.	0.5	0